PARTICLE SIZE DETERMINATION

Apply the carious methods for determining particle sizes in different structures. photo are various dispersed in a matrix, the distance between them are greater than a photographic backing at it in a minute size of a migropator. the distance between them are greater than the size of a micrometer-sized grain can be size of a high half of a transfer on the size of a micrometer-sized grain can be A think the help of a transmission electron microscope and anosized particle is meroscope. The size of a nanosized graphined with the help of a transmission electron microscope (TEM). the manner in which particles scatter light provides a means of determining

the scattering amplitude is a function of relationship between particle who light reflected from the sky during the derivation of the incident light the light reflected from the sky during the day appears blue whereas that the har the atmosphere at sunrise and sunset appears red. This is because whitering cross-section σ is proportional to $\frac{1}{\lambda^4}$. So blue colour of light is

whereas the scattering for red colour is least.

particle size is determined by using a monochromatic laser beam scattered at a which angle (usually 90°) for parallel and perpendicular polarizations. The intensities can give information regarding particle size, particle particles and the refractive index. For particles with size $d < 0.1\lambda$, size of whitele is measured with optical wavelengths. The method of laser beam manufactive determination is applicable for nanoparticle with diameters greater Att 2 tisk

The method of mass spectrometry is used for particle size determination for with diameters less than 2 nm. The schematic diagram of gas mass potrometer is shown in fig. 6.3.

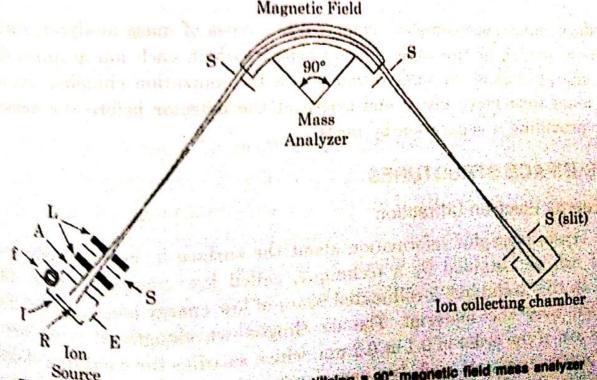


Fig. 6.3. Sketch of a mass spectrometer utilizing a 90° magnetic field mass analyzer In it, the nanoparticles are ionized to form positive ions by the impact of the nanoparticles are ionized to torm positive long the ion emitted from the heated filament in the ionization chamber of the ion Scanned with CamSc

source. These ions are accelerated through a voltage V between the repeller of source. These ions are accelerated through a voltage V between the repeller of source. These ions are accelerated through a voltage V between the repeller of source. The magnetic field p source. These ions are accelerated through a voltage by lenses L and then colling accelerator (A) plates. After it, they are focused by lenses L and then colling accelerator (A) plates. After it, they are focused by lenses L and then colling accelerator (A) plates. After it, they are focused by lenses L and then colling to the mass analyzer. The magnetic field B, oright. source. These ions are it, they are focused. The magnetic field B_i colling accelerator (A) plates. After it, they are focused. The magnetic field B_i colling slits S during their transit to the mass analyzer. The magnetic field B_i oriented states and the ion beam through some E and E and E and E are the ion with slits S during their transit to the mass and bends the ion beam through the page exerts a magnetic force F = qvB and bends the ion beam through the page exerts a magnetic force F = qvB and bends the ion collector. of 90° at the radius r, after with they are detected at the ion collector.

The necessary centripetal force $\left(\frac{mv^2}{r}\right)$ is provided by the magnetic force

On balancing these forces, we get

or
$$\frac{mv^2}{r} = qvB$$

$$2m \times \frac{1}{2}mv^2 = q^2B^2r^2$$
or
$$2m \times qV = q^2B^2r^2$$
or
$$\frac{m}{q} = \frac{B^2r^2}{2V}$$

which gives the mass to charge ratio of the particles (ions).

In a particular instrument, r is fixed. So either magnetic field B or accelerate voltage V can be scanned to focus the ions of different masses at the detector. Sime is generally known for nanosized ion, therefore m can be determined. Further, b material forming the nanoparticle is known, thus its density $\rho = m/V$ is known. Her V represents the volume of the material. Therefore its size or linear dimension $d = (V)^{1/3} = (m/\rho)^{1/3}$ can be determined.

Modern mass spectrometers employ other types of mass analyzer, such as the quadrupole model, or the time of flight type in which each ion acquires the same kinetic energy during its acceleration out of the ionization chamber. As a result lighter mass ions move faster and arrive at the detector before the heavier ions thereby providing a separation by mass.

→ 6.5. SURFACE STRUCTURES

I. Low Energy Electron Diffraction

The crystallographic information about the surface layers of single-crystalling erial can be obtained by a technique. material can be obtained by a technique, called low energy electron diffraction (LEED). In this technique a collimated beautiful to a collimated bea (LEED). In this technique a collimated beam of low energy electron combarded over the material. The de Day energy electrons (20-200 eV) bombarded over the material. The de Broglie wavelength of such low energy electrons (20-zov electrons are of the order of 0.1 or 0.2 nm which electrons are of the order of 0.1 or 0.2 nm, which satisfies the condition of diffraction atomic structures. At such low energies 41 on atomic structures. At such low energies the satisfies the condition of dimensions into the surface, so their diffraction resitions penetrate only very short conditions. listances into the surface, so their diffraction pattern reflects the atomic positions are some surface layer. Diffracted electrons are some surface the atomic positions are some surface. he surface layer. Diffracted electrons are seen as spots on fluorescent screen tensities of diffracted beams are recorded as a function of incident electron

Scarried with CarriSca

energy to generate I-V curves. These curves are then compared with theoretical curves to provide information on atomic positions on the surface in question.

If the diffraction pattern arises from more than one surface layer, the contribution of lower lying crystallographic planes will be weaker in intensity. The electron beam behaves like a wave and is therefore reflected from crystallographic planes in the same manner as an X-ray beam. The electron de-Broglie wavelength is given by

$$\lambda = \frac{1.226 \times 10^{-9}}{\sqrt{E}} \text{m} = \frac{1.226}{\sqrt{E}} \text{nm}$$

where E is the energy of electrons in units of electron volt. For example an electron energy of 25.2 eV corresponds to a de Broglie wavelength of 0.2442 nm. This wavelength is comparable with the GaAs bond distance in gallium arsenide $\left(\frac{a\sqrt{3}}{4}=0.2442\,\mathrm{nm}\right)$, with lattice constant $a=0.565\,\mathrm{nm}$. Thus low energy electron

diffraction experiments are capable of providing accurate information about surface structure of materials. In this method the sample itself must be a single crystal with structure of materials. In this method the sample itself must be a single crystal with swell ordered surface structure in order to generate a back scattered electron diffraction pattern

-------- Diffraction